G2R1000MT17D
1700 V 1000 mΩ SiC MOSFET

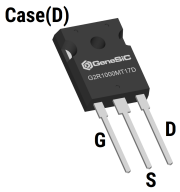
Silicon Carbide MOSFET
N-Channel Enhancement Mode

V_{DS}	=	1700 V
$R_{DS(ON)(Typ.)}$	=	1000 mΩ
I_D (T_C = 100°C)	=	4 A

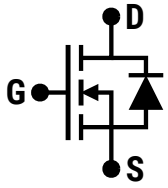
Features

- G2R™ Technology - +20 V / -5 V Gate Drive
- Superior Q_G x $R_{DS(ON)}$ Figure of Merit
- Low Capacitances and Low Gate Charge
- High V_{th} for Increased System Stability
- Fast and Reliable Body Diode
- High Avalanche and Short Circuit Ruggedness
- Low Conduction Losses at High Temperatures

Package



TO-247-3



D = Drain
G = Gate
S = Source

RoHS

REACH

Advantages

- Increased Power Density for Compact System
- High Frequency Switching
- Reduced Losses for Higher System Efficiency
- Minimized Gate Ringing
- Improved Thermal Capability
- Superior Cost-Performance Index
- Ease of Paralleing without Thermal Runaway
- Simple to Drive

Applications

- Auxiliary Power Supply
- Switched Mode Power Supplies
- High Voltage Converters
- Pulsed Power

Absolute Maximum Ratings (At T_C = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	$V_{DS(max)}$	V_{GS} = 0 V, I_D = 100 µA	1700	V	
Gate-Source Voltage (Dynamic)	$V_{GS(max)}$		-10 / +25	V	
Gate-Source Voltage (Static)	$V_{GS(op)}$	Recommended Operation	-5 / +20	V	
Continuous Forward Current	I_D	T_C = 100°C, V_{GS} = -5 / +20 V T_C = 135°C, V_{GS} = -5 / +20 V	4 3	A	Fig. 14
Pulsed Drain Current	$I_{D(pulse)}$	t_P ≤ 10µs, D ≤ 1%, Note 1	8	A	Fig. 13
Power Dissipation	P_D	T_c = 25°C	53	W	Fig. 15
Operating and Storage Temperature	T_j , T_{stg}		-55 to 175	°C	

Thermal/Package Characteristics

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Thermal Resistance, Junction - Case	R_{thJC}			2.39	2.83	°C/W	Fig. 12
Weight	W_T			6.1		g	
Mounting Torque	T_M	Screws to Heatsink			1.1	Nm	

Note 1: Pulse Width t_P Limited by $T_{j(max)}$

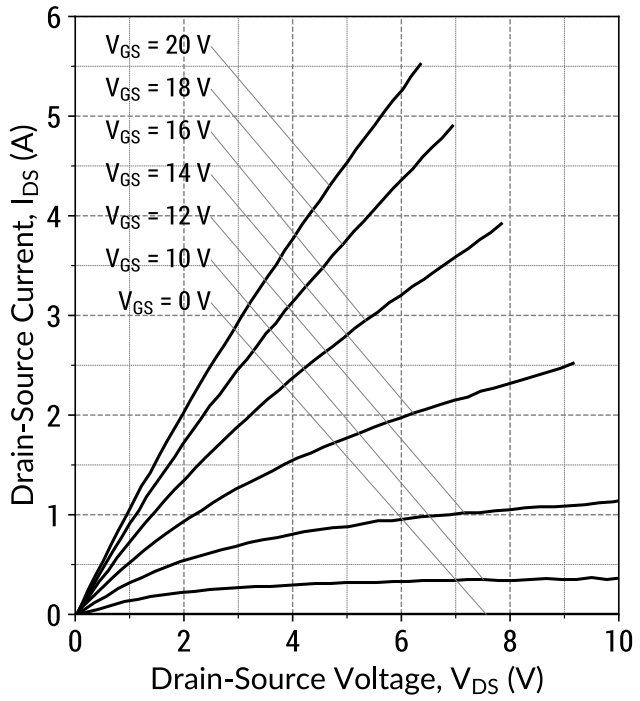
Electrical Characteristics (At T_C = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	V_{DSS}	V_{GS} = 0 V, I_D = 100 µA	1700			V	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1700 V, V_{GS} = 0 V		1		µA	
Gate Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 25 V V_{DS} = 0 V, V_{GS} = -10 V			100 -100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 2 mA V_{DS} = V_{GS}, I_D = 2 mA, T_j = 175°C	3.3	4 3		V	Fig. 9
Transconductance	g_{fs}	V_{DS} = 10 V, I_D = 2 A V_{DS} = 10 V, I_D = 2 A, T_j = 175°C		0.74 0.71		S	Fig. 4
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 20 V, I_D = 2 A V_{GS} = 20 V, I_D = 2 A, T_j = 175°C		1000 1680	1200	mΩ	Fig. 5-8
Input Capacitance	C_{iss}	V_{DS} = 1000 V, V_{GS} = 0 V f = 1 MHz, V_{AC} = 25mV		139		pF	Fig. 10
Output Capacitance	C_{oss}			22			
Reverse Transfer Capacitance	C_{rss}			6.2			
C_{oss} Stored Energy	E_{oss}			15		µJ	Fig. 11
C_{oss} Stored Charge	Q_{oss}			27		nC	
Internal Gate Resistance	$R_{G(int)}$	f = 1 MHz, V_{AC} = 25 mV		5		Ω	

Reverse Diode Characteristics

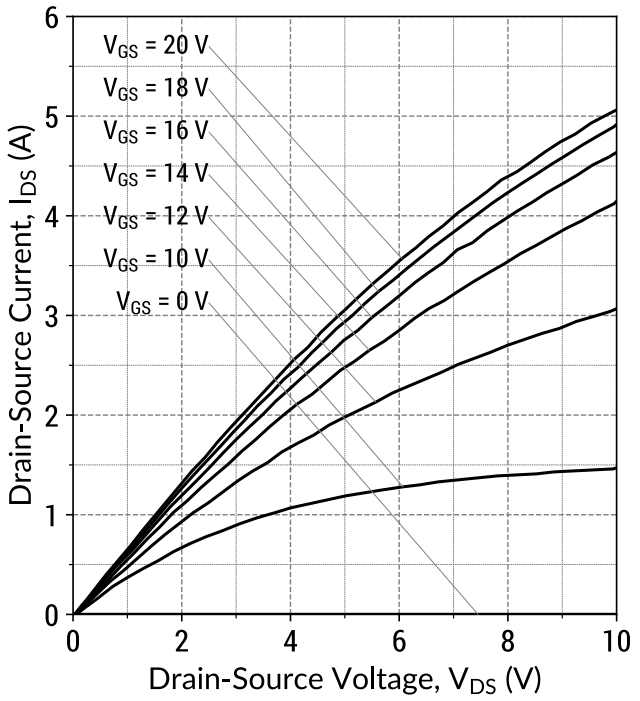
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}	V_{GS} = -5 V, I_{SD} = 1 A V_{GS} = -5 V, I_{SD} = 1 A, T_j = 175°C		4 3.5		V	Fig. 16-17
Continuous Diode Forward Current	I_S	V_{GS} = -5 V, T_c = 100°C	4			A	
Diode Pulse Current	$I_{S(pulse)}$	V_{GS} = -5 V, Note 1		16		A	

Figure 1: Output Characteristics (T_j = 25°C)



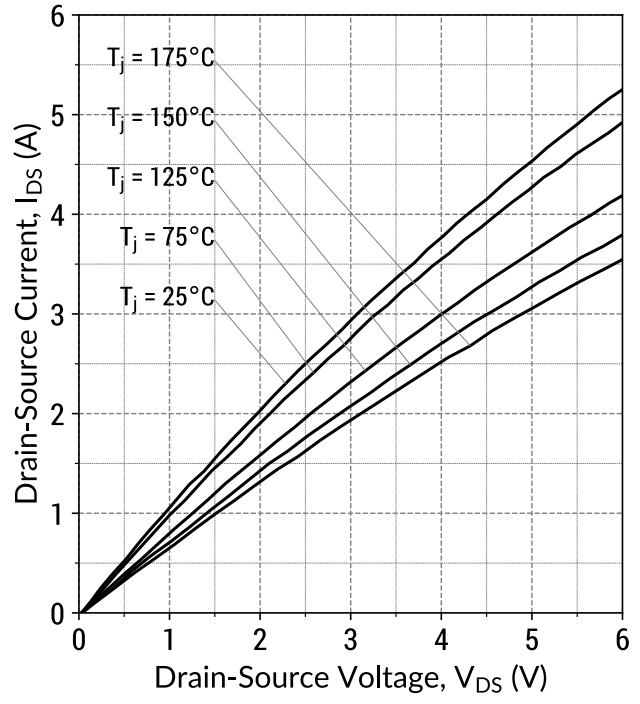
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 2: Output Characteristics (T_j = 175°C)



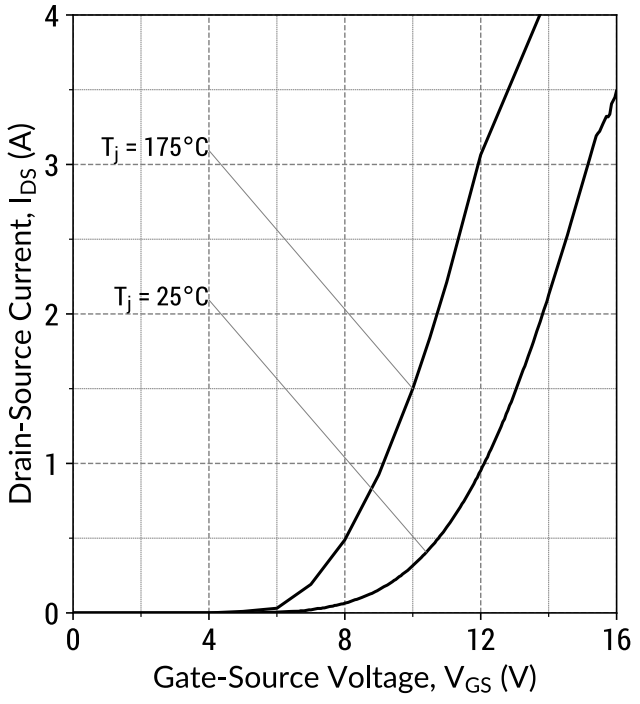
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 3: Output Characteristics (V_{GS} = 20 V)



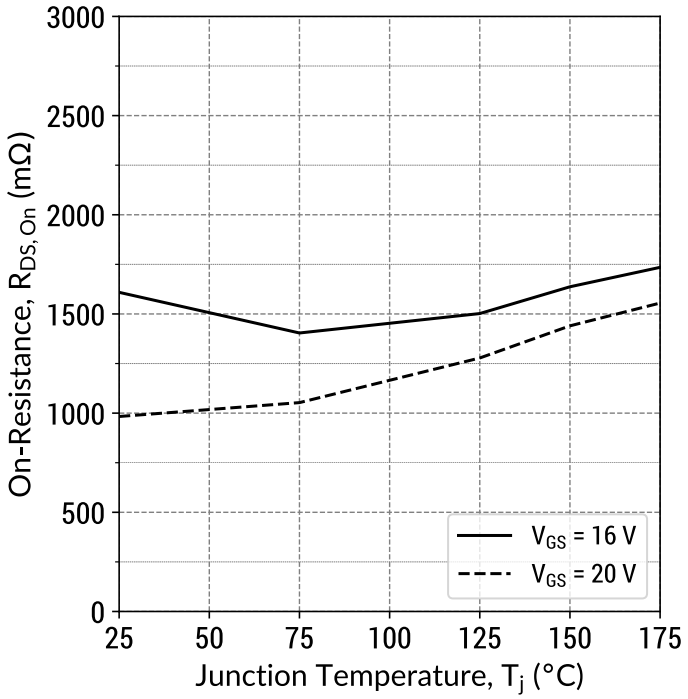
$I_D = f(V_{DS}, T_j)$; t_P = 250 µs

Figure 4: Transfer Characteristics (V_{DS} = 10 V)



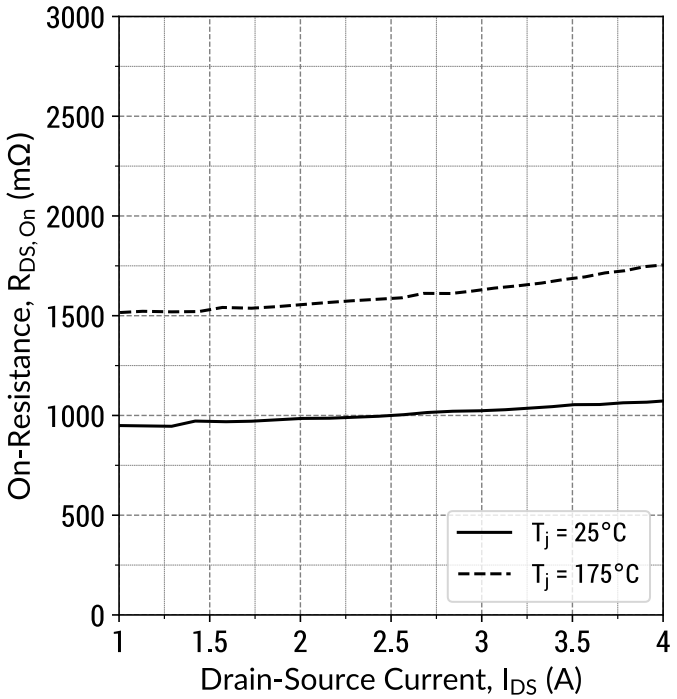
$I_D = f(V_{GS}, T_j)$; t_P = 100 µs

Figure 5: On-State Resistance v/s Temperature



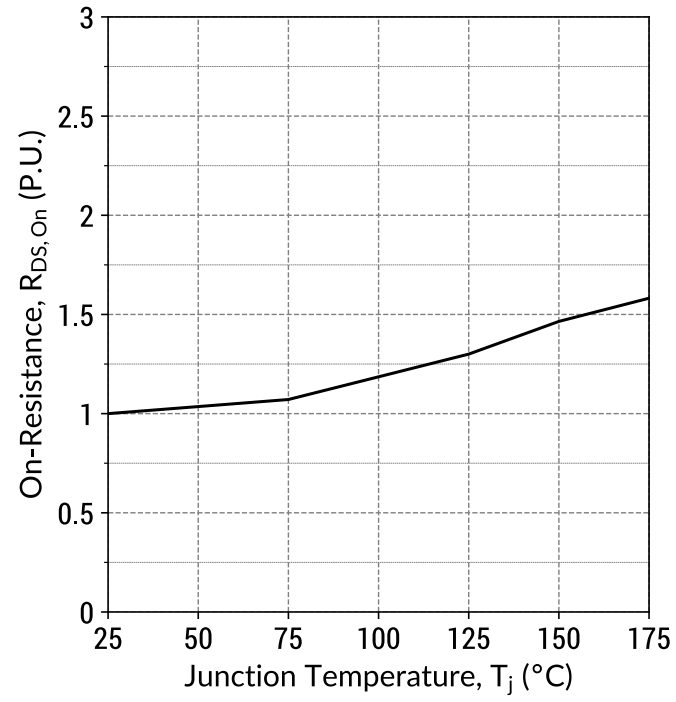
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 2 A

Figure 6: On-State Resistance v/s Drain Current



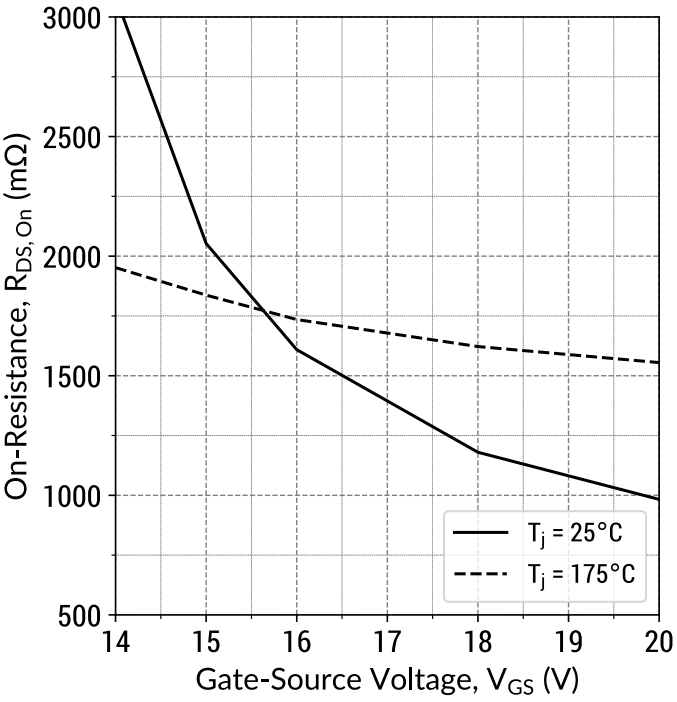
$R_{DS(ON)} = f(T_j, I_D)$; t_P = 250 µs; V_{GS} = 20 V

Figure 7: Normalized On-State Resistance v/s Temperature



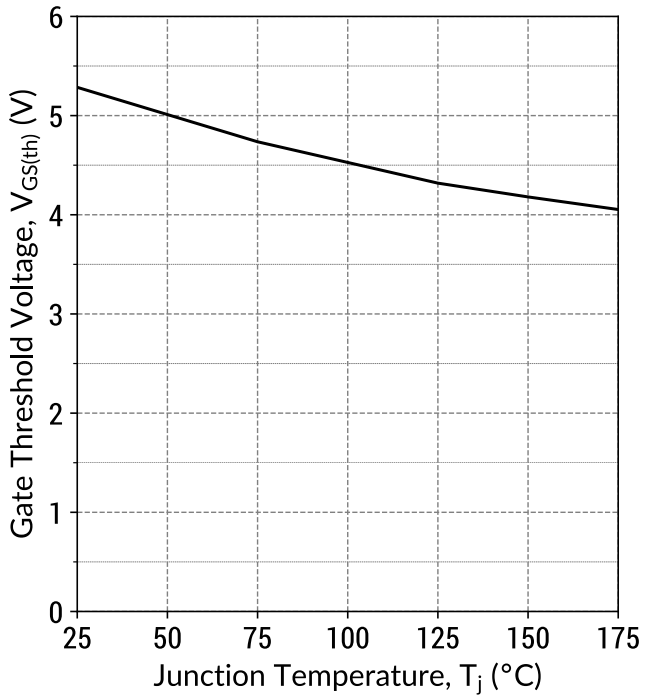
$R_{DS(ON)} = f(T_j)$; t_P = 250 µs; I_D = 2 A; V_{GS} = 20 V

Figure 8: On-State Resistance v/s Gate Voltage



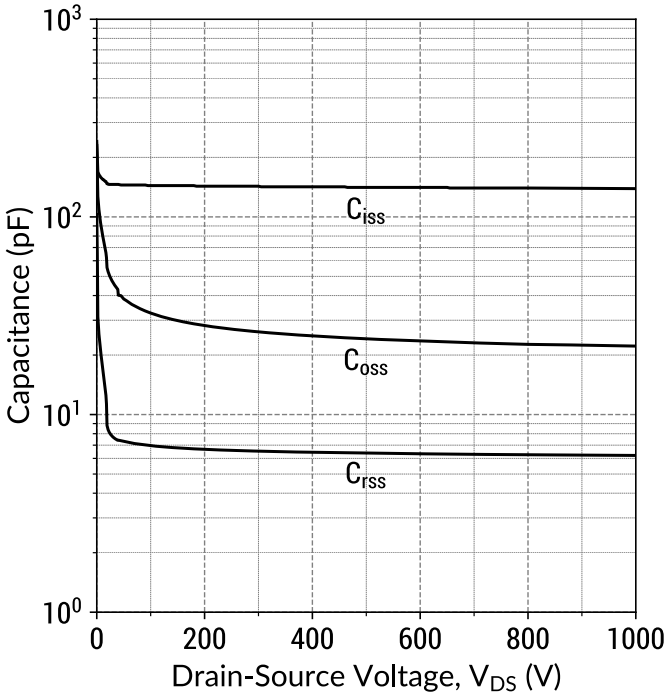
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 2 A

Figure 9: Threshold Voltage Characteristics



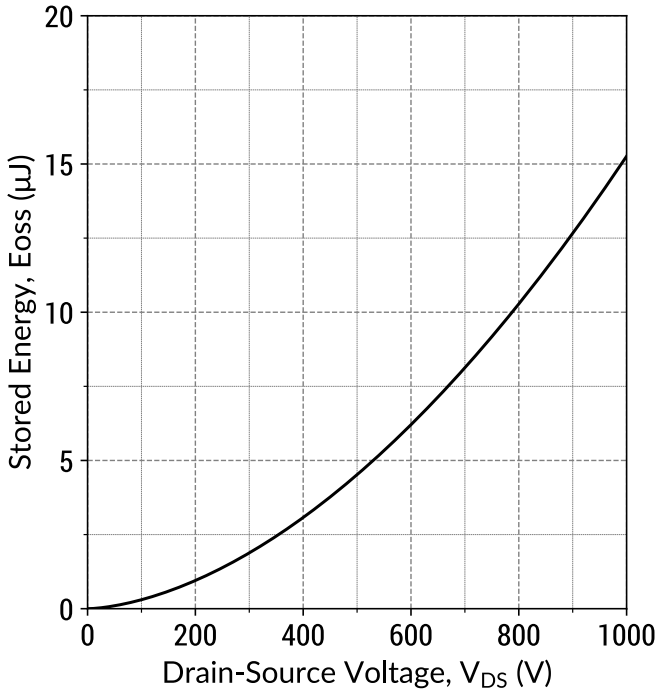
$V_{GS(th)} = f(T_j)$; $V_{DS} = V_{GS}$; I_D = 2 mA

Figure 10: Capacitance v/s Drain-Source Voltage



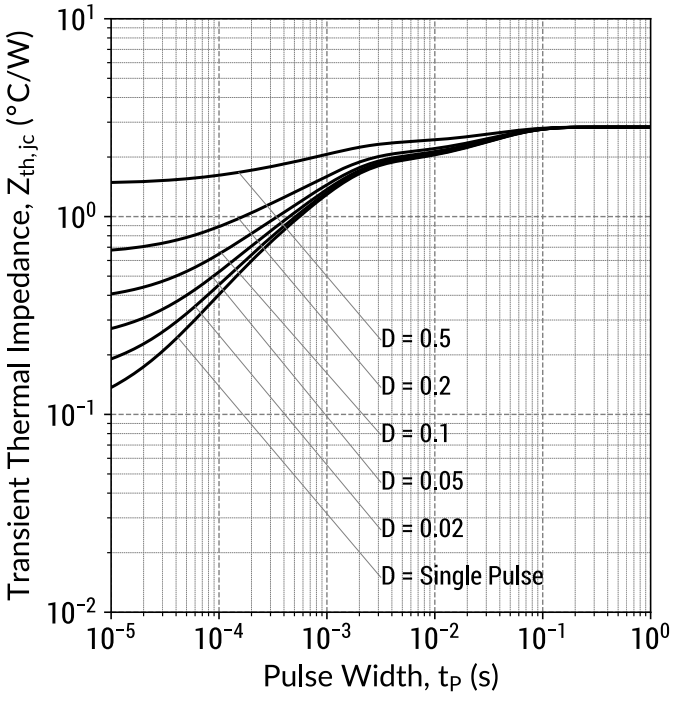
f = 1 MHz; V_{AC} = 25mV

Figure 11: Output Capacitor Stored Energy



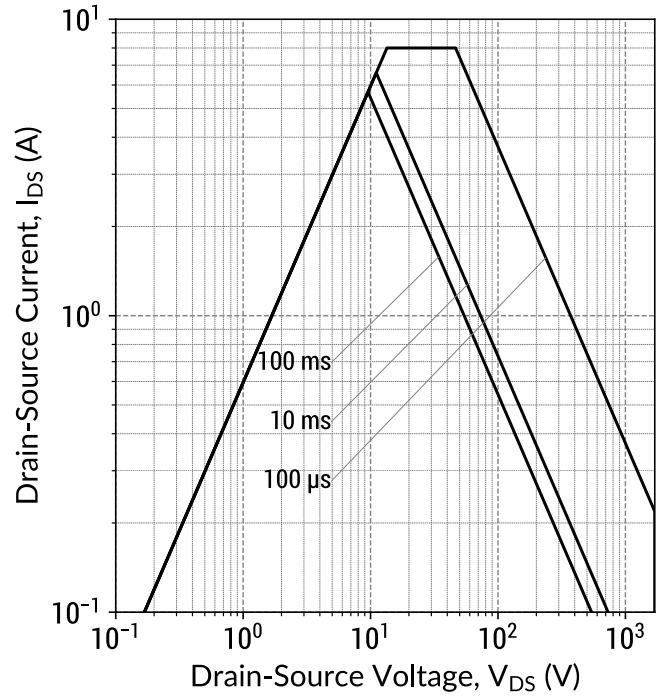
$E_{oss} = f(V_{DS})$

Figure 12: Transient Thermal Impedance



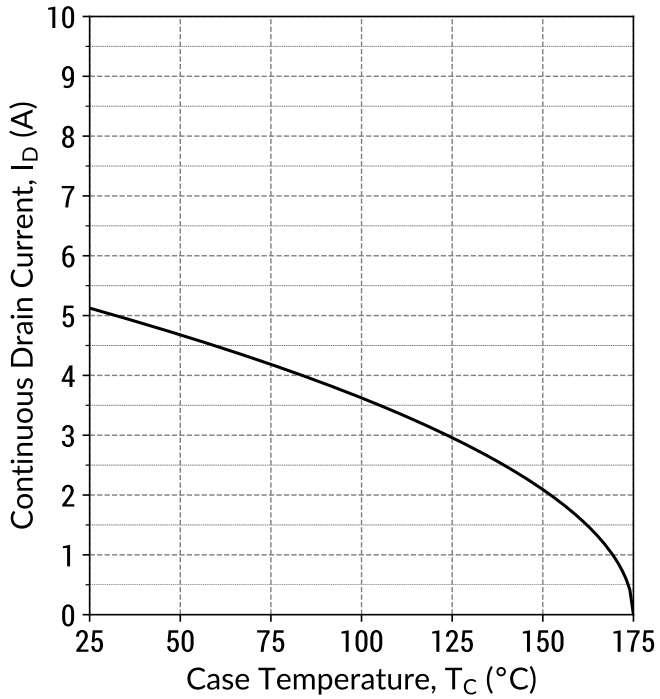
$Z_{th,jc} = f(t_P,D)$; $D = t_P/T$

Figure 13: Safe Operating Area (T_c = 25°C)



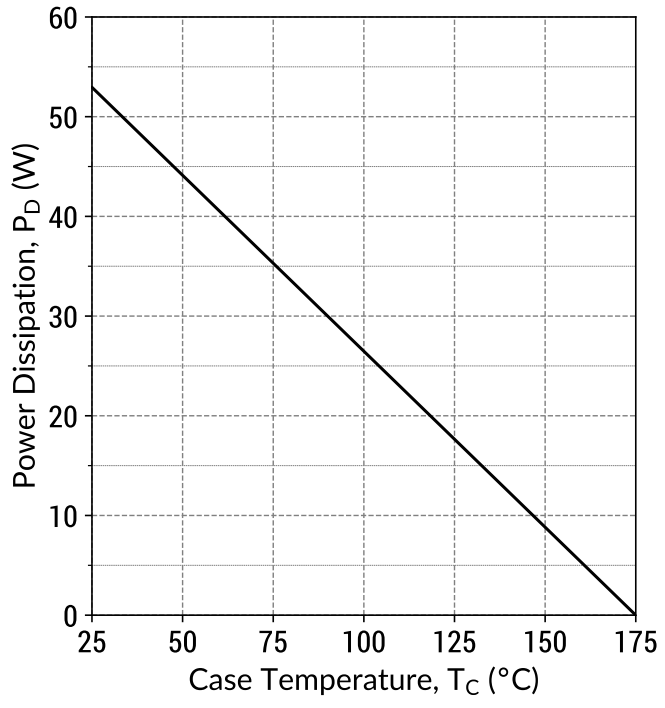
$I_D = f(V_{DS}, t_P)$; $T_j \leq 175°C$; D = 0

Figure 14: Current De-rating Curve



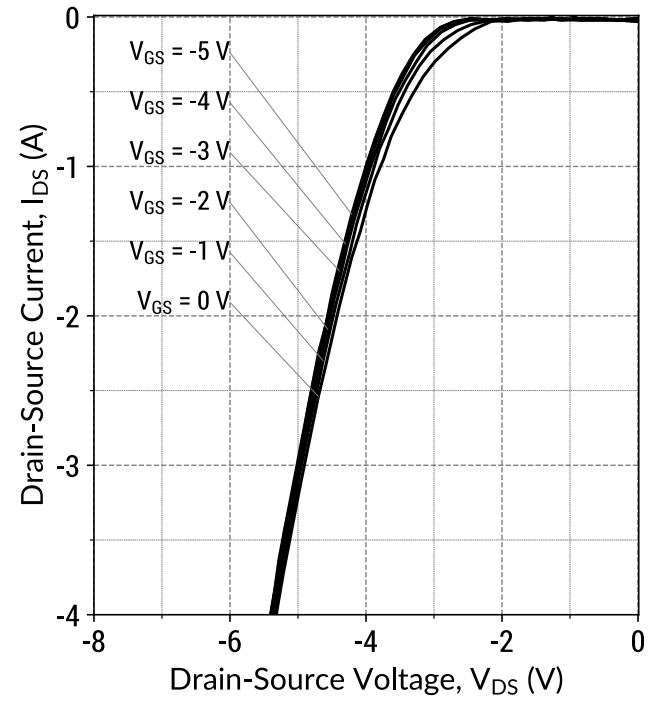
$I_D = f(T_C)$; $T_j \leq 175°C$

Figure 15: Power De-rating Curve



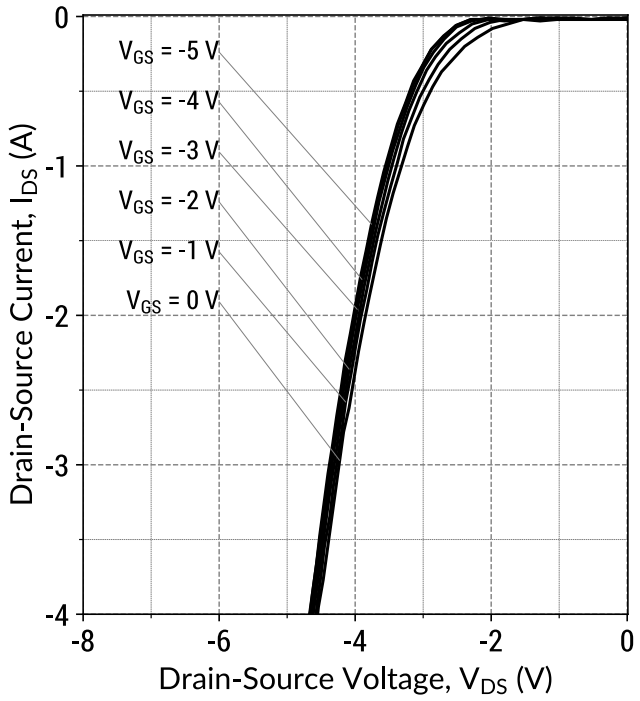
$P_D = f(T_C)$; $T_j \leq 175°C$

Figure 16: Body Diode Characteristics (T_j = 25°C)



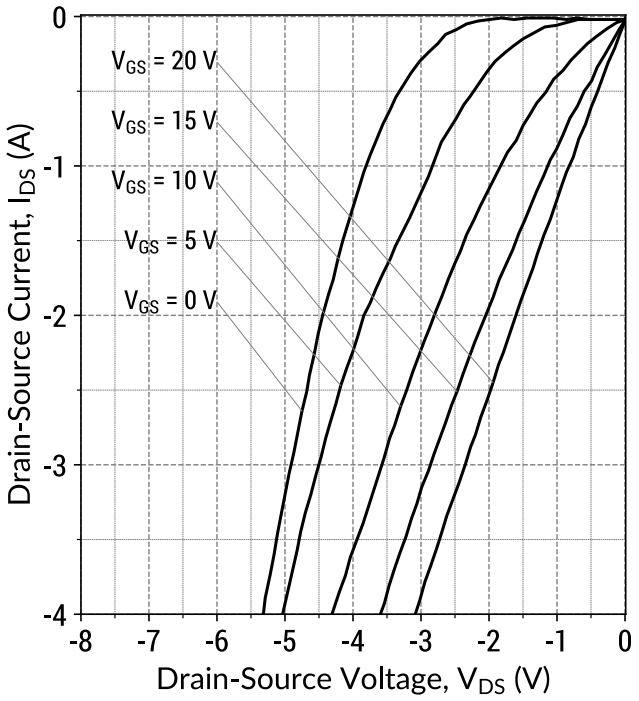
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 17: Body Diode Characteristics (T_j = 175°C)



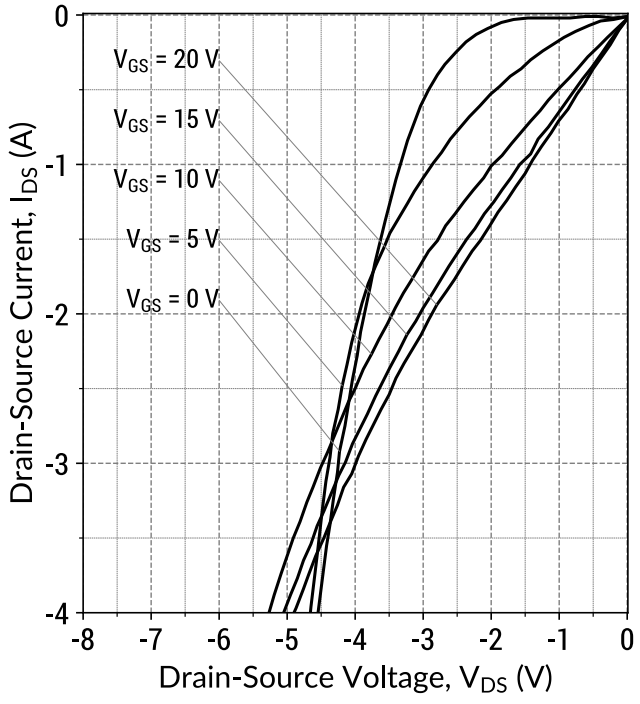
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 18: Third Quadrant Characteristics (T_j = 25°C)



$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

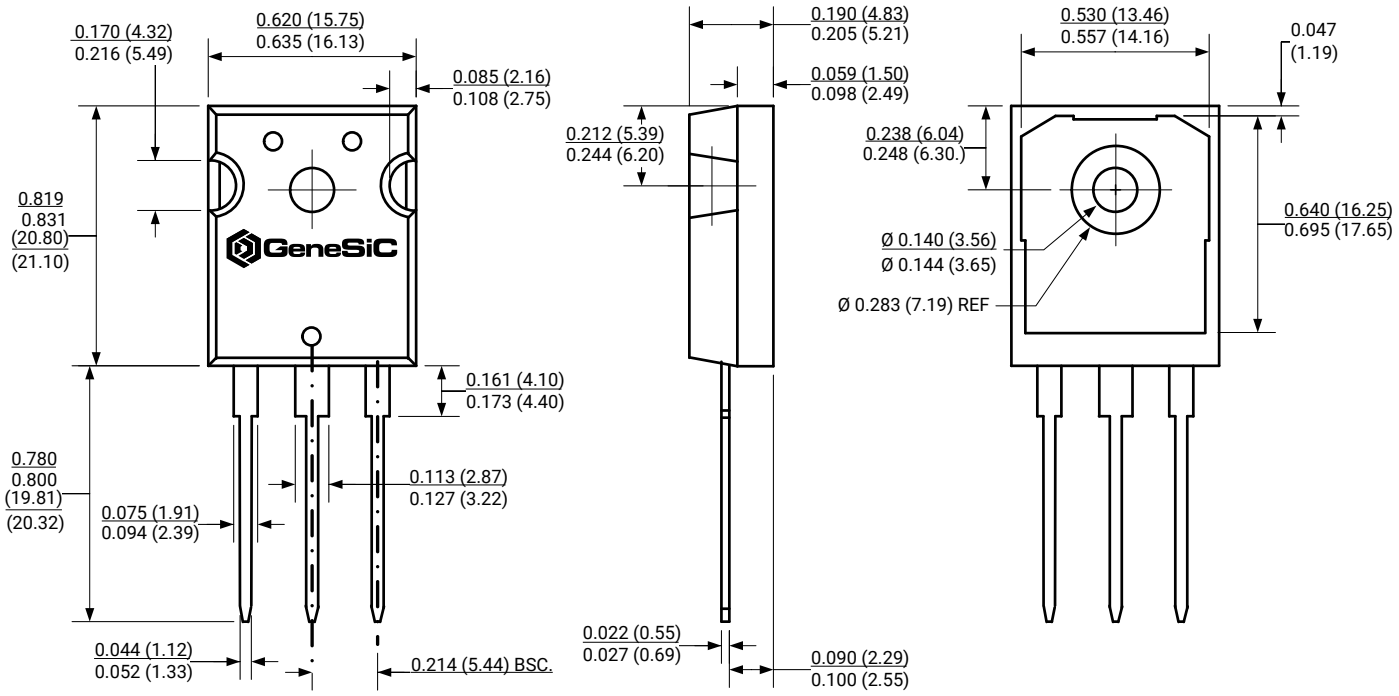
Figure 19: Third Quadrant Characteristics (T_j = 175°C)



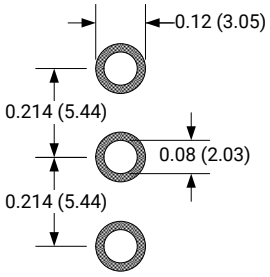
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Package Dimensions

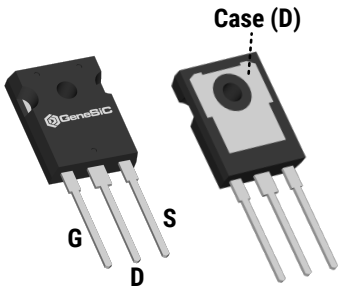
TO-247-3 Package Outline



Recommended Solder Pad Layout



Package View



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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Related Links

- SPICE Models: https://www.genesicsemi.com/sic-mosfet/G2R1000MT17D/G2R1000MT17D_SPICE.zip
- PLECS Models: https://www.genesicsemi.com/sic-mosfet/G2R1000MT17D/G2R1000MT17D_PLECS.zip
- CAD Models: https://www.genesicsemi.com/sic-mosfet/G2R1000MT17D/G2R1000MT17D_3D.zip
- Gate Driver Reference: https://www.genesicsemi.com/technical-support
- Evaluation Boards: https://www.genesicsemi.com/technical-support
- Reliability: https://www.genesicsemi.com/reliability
- Compliance: https://www.genesicsemi.com/compliance
- Quality Manual: https://www.genesicsemi.com/quality

Revision History

Date	Revision	Comments	Supersedes
Aug. 3, 2020	Rev 2	Part Number Changed from G3R1000MT17D to G2R1000MT17D	Rev 1
Jun. 2, 2020	Rev 1	Initial Release	

www.genesicsemi.com/sic-mosfet/

Published by GeneSiC Semiconductor, Inc.
43670 Trade Center Place Suite 155, Dulles, VA 20166; USA